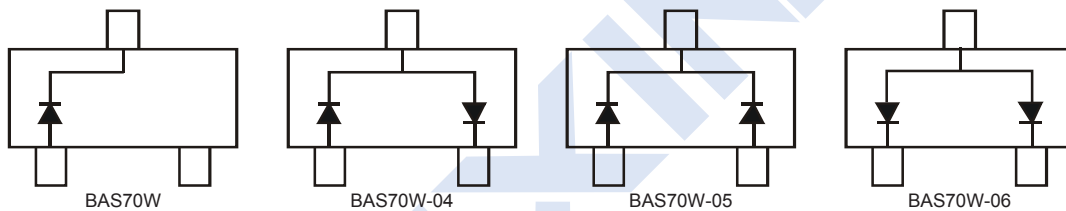
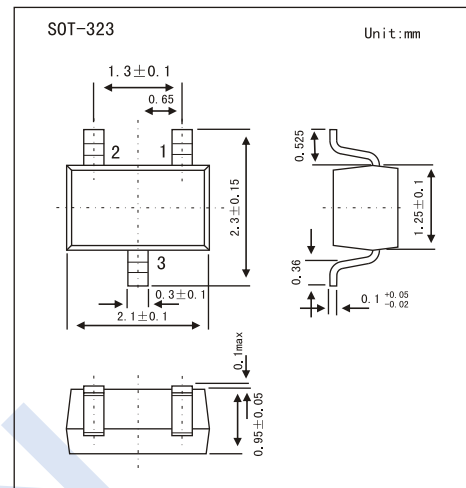


Schottky Barrier Diodes

BAS70W /-04 /-05 /-06

■ Features

- Low forward voltage
- High breakdown voltage
- Guard ring protected
- Very small SMD package
- Low capacitance.

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Rating	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	70	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	49	
Continuous Forward Current (Note 1)	I_F	70	mA
Non-Repetitive Peak Forward Surge Current @ $t_p < 1.0\text{s}$	I_{FSM}	100	
Power Dissipation (Note 1)	P_D	200	mW
Thermal Resistance Junction to Ambient (Note 1)	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

Note 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

■ Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage (Note 2)	V_R	$I_R = 10\mu\text{A}$	70			V
Forward voltage	V_F	$I_F = 1\text{mA}$			410	mV
		$I_F = 10\text{mA}$			750	
		$I_F = 15\text{mA}$			1000	
Reverse current (Note 2)	I_R	$V_R = 50\text{V}$			100	nA
		$V_R = 70\text{V}$			10	μA
Total Capacitance	C_T	$V_R = 0\text{V}$, $f = 1\text{MHz}$			2	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10\text{mA}$ to $I_R = 1\text{mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100\Omega$			5	ns

Note 2. Pulse test: $t_p = 300\text{ms}$; $d = 0.02$

Schottky Barrier Diodes

BAS70W /-04 /-05 /-06

■ Marking

Type	BAS70W	BAS70W-04	BAS70W-05	BAS70W-06
Marking	K73	K74	K75	K76

■ Typical Characteristics

